

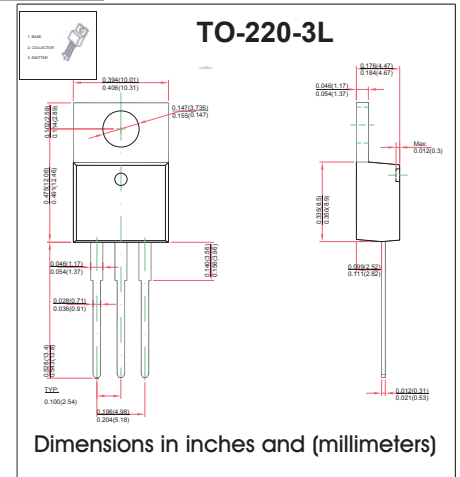
## TO-220-3L Plastic-Encapsulate MOSFETS

### FEATURE

- N-Channel Power MOSFET
- High Current Rating
- Lower RDS(on)
- Lower Capacitance
- Lower Total Gate Charge
- Tighter VSD Specifications
- Avalanche Energy Specified

### MECHANICAL DATA

- Case style:TO-220-3L molded plastic
- Mounting position:any



## MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	600	V
Gate-Source Voltage	$V_{GS}$	$\pm 30$	
Continuous Drain Current	$I_D$	8	A
Pulsed Drain Current	$I_{DM}$	32	
Single Pulsed Avalanche Energy (note1)	$E_{AS}$	250	mJ
Power Dissipation	$P_D$	2	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	62.5	°C/W
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 ~ +150	°C
Maximum lead temperature for soldering purposes , Duration 5 seconds	$T_L$	260	

## MOSFET ELECTRICAL CHARACTERISTICS $T_A=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Off characteristics</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	600			V
Drain-source diode forward voltage(note2)	$V_{SD}$	$V_{GS} = 0V, I_S = 7A$			1.4	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 600V, V_{GS} = 0V$			1	$\mu A$
Gate-body leakage current (note2)	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 30V$			$\pm 100$	nA
<b>On characteristics (note2)</b>						
Gate-threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0		4.0	V
Static drain-source on-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 4A$			1.3	$\Omega$
<b>Dynamic characteristics (note 3)</b>						
Input capacitance	$C_{iss}$	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$			1280	pF
Output capacitance	$C_{oss}$				120	
Reverse transfer capacitance	$C_{rss}$				11	
<b>Switching characteristics (note 3)</b>						
Turn-on delay time (note3)	$t_{d(on)}$	$V_{DD} = 300V, V_{GS} = 10V,$ $R_G = 25\Omega, I_D = 7A$			80	ns
Turn-on rise time (note3)	$t_r$				165	
Turn-off delay time (note3)	$t_{d(off)}$				160	
Turn-off fall time (note3)	$t_f$				120	

### Notes :

1.  $I_L = 8A, V_{DD} = 50V, R_G = 25\Omega, \text{Starting } T_J = 25^\circ\text{C}.$
2. Pulse Test : Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
3. These parameters have no way to verify.